Silicon PNP transistor epitaxial type
AP089

[Applications]
General purpose

[Feature]
Low collector saturation voltage VCE(sat)= -0.4V(Max.) at IC= -50mA, IB= -5mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-40	V
Emitter-base voltage	VEBO	-5	V
Collector current	IC	-0.2	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-40	-	-	V	IC= -10uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-40	-	-	V	IC= -10mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-5	-	-	V	IE= -10uA, IC= 0A
DC current gain 1	hFE 1	60	-	-	-	VCE= -1V, IC= -0.1mA
DC current gain 2	hFE 2	80	-	-	-	VCE= -1V, IC= -1mA
DC current gain 3	hFE 3	90	-	333	-	VCE= -1V, IC= -10mA
DC current gain 4	hFE 2	60	-	-	-	VCE= -1V, IC= -50mA
DC current gain 5	hFE 3	30	-	-	-	VCE= -1V, IC= -100mA
Collector-emitter saturation voltage 1	VCE(sat) 1	-	-	-0.25	V	IC= -10mA, IB= -1mA
Collector-emitter saturation voltage 2	VCE(sat) 2	-	-	-0.4	V	IC= -50mA, IB= -5mA
Transition frequency	fT	250	-	-	MHz	VCE= -20V, IE= 10mA
Collector output capacitance	Cob	-	-	4	pF	VCB= -5V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.
Notice 2) The contents described herein are subject to change without notice.